



US00D773412S

(12) **United States Design Patent** (10) **Patent No.:** **US D773,412 S**
Yoneyama et al. (45) **Date of Patent:** **** Dec. 6, 2016**

(54) **SEMICONDUCTOR DEVICE**

H02B 6/4201; G02B 6/4256; G02B 6/4257;
G02B 6/4261; G02B 6/4262; G02B 6/428;
G02B 6/4281; H05K 1/14; H05K 1/141;
H05K 1/142; H05K 1/144; H05K 1/18;
H05K 1/181; H05K 1/182

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See application file for complete search history.

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(**) Term: **15 Years**

(21) Appl. No.: **29/567,910**

(22) Filed: **Jun. 14, 2016**

Related U.S. Application Data

(62) Division of application No. 29/531,173, filed on Jun. 23, 2015, now Pat. No. Des. 766,851.

(30) **Foreign Application Priority Data**

Feb. 4, 2015 (JP) 2015-002059
Feb. 4, 2015 (JP) 2015-002061

(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**

USPC D13/182
CPC H01L 21/00; H01L 21/02433; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4814; H01L 21/4846; H01L 21/4871; H01L 21/67144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L 2924/17151; H01L 2924/181; H01L 2924/1811; H01L 2924/1815; H01L 2924/1905; H01L 29/04; H01L 2224/08054; H01L 23/58; H05B 41/14;

(Continued)

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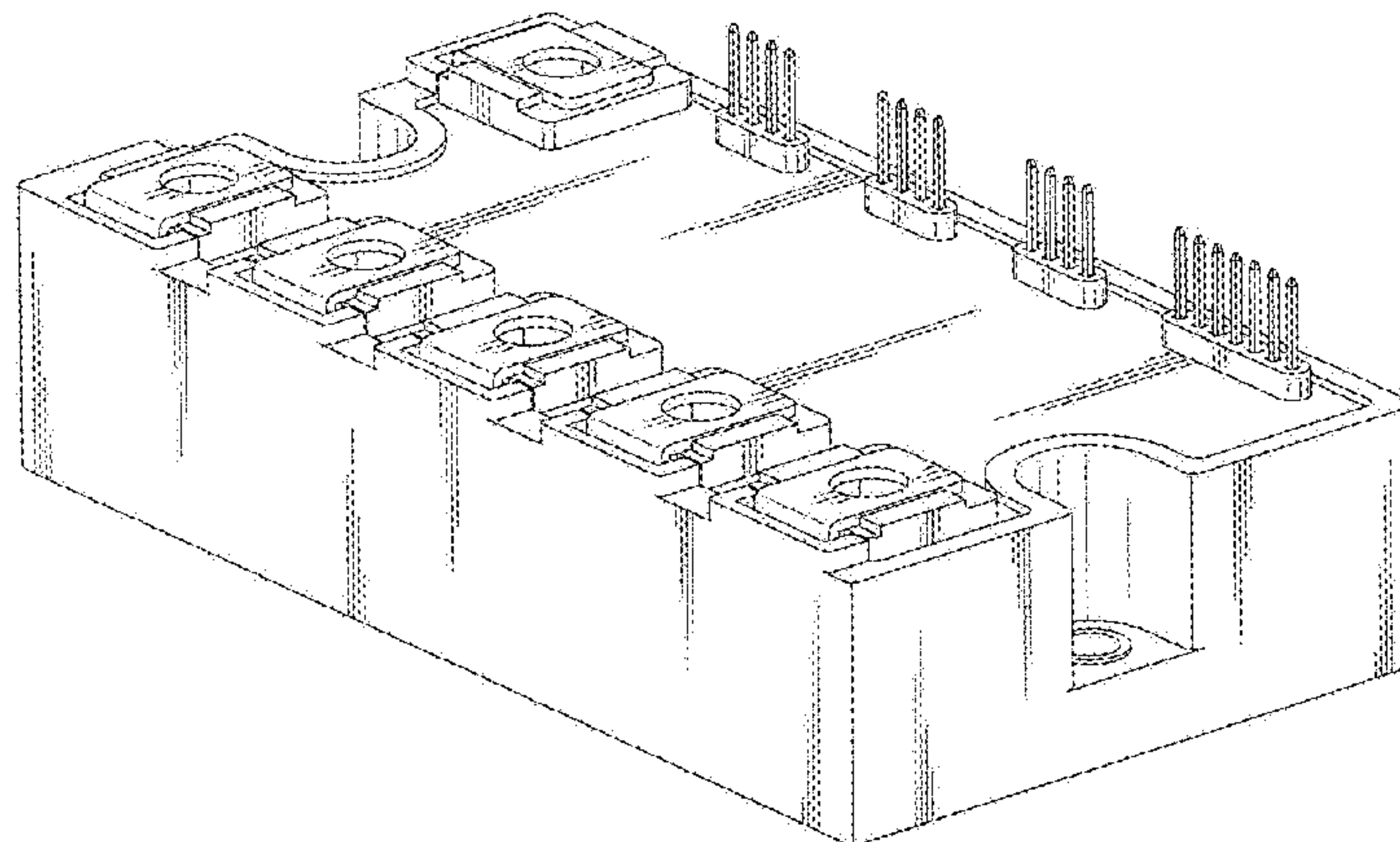
(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. 1 is a front, top and right side perspective view of a semiconductor device, showing our new design;
FIG. 2 is a front view thereof;
FIG. 3 is a rear view thereof;
FIG. 4 is a left side view thereof;
FIG. 5 is a right side view thereof;
FIG. 6 is a top view thereof; and,
FIG. 7 is a bottom view thereof.

1 Claim, 7 Drawing Sheets



(56)

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Fig. 1

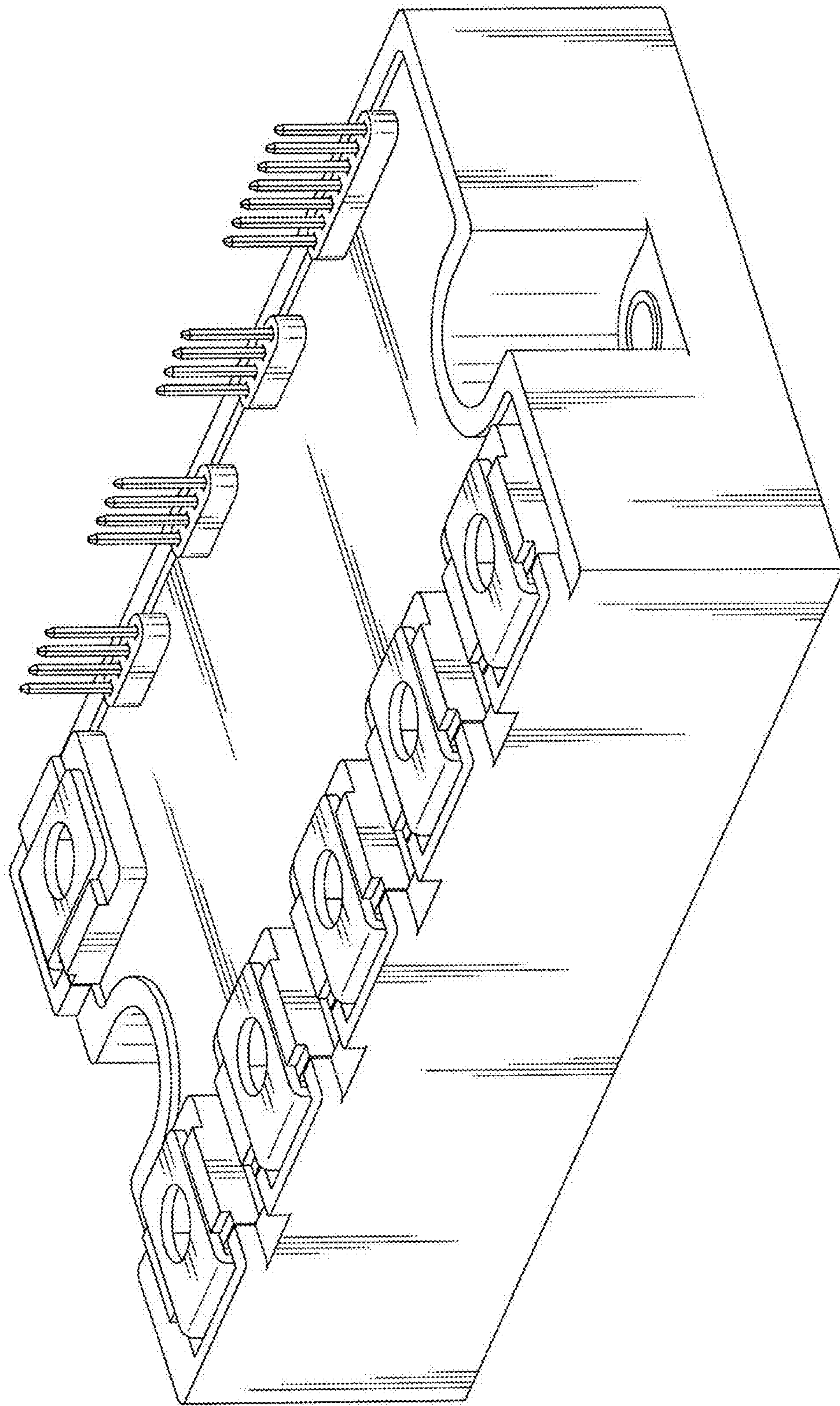


Fig. 2

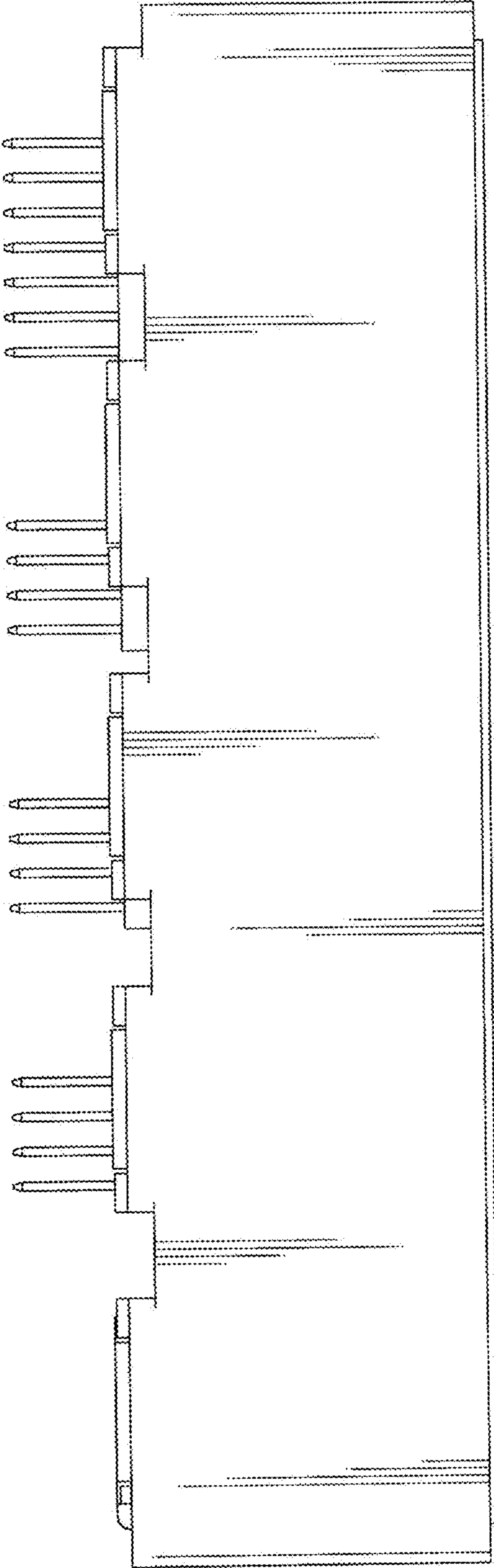


Fig. 3

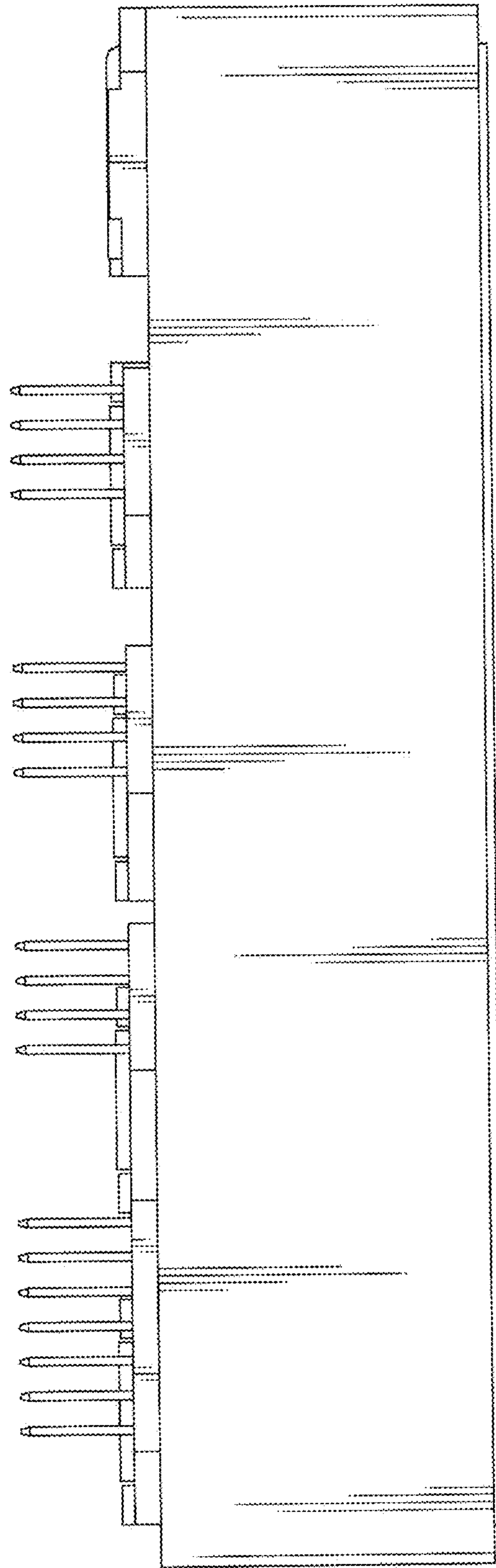


Fig. 4

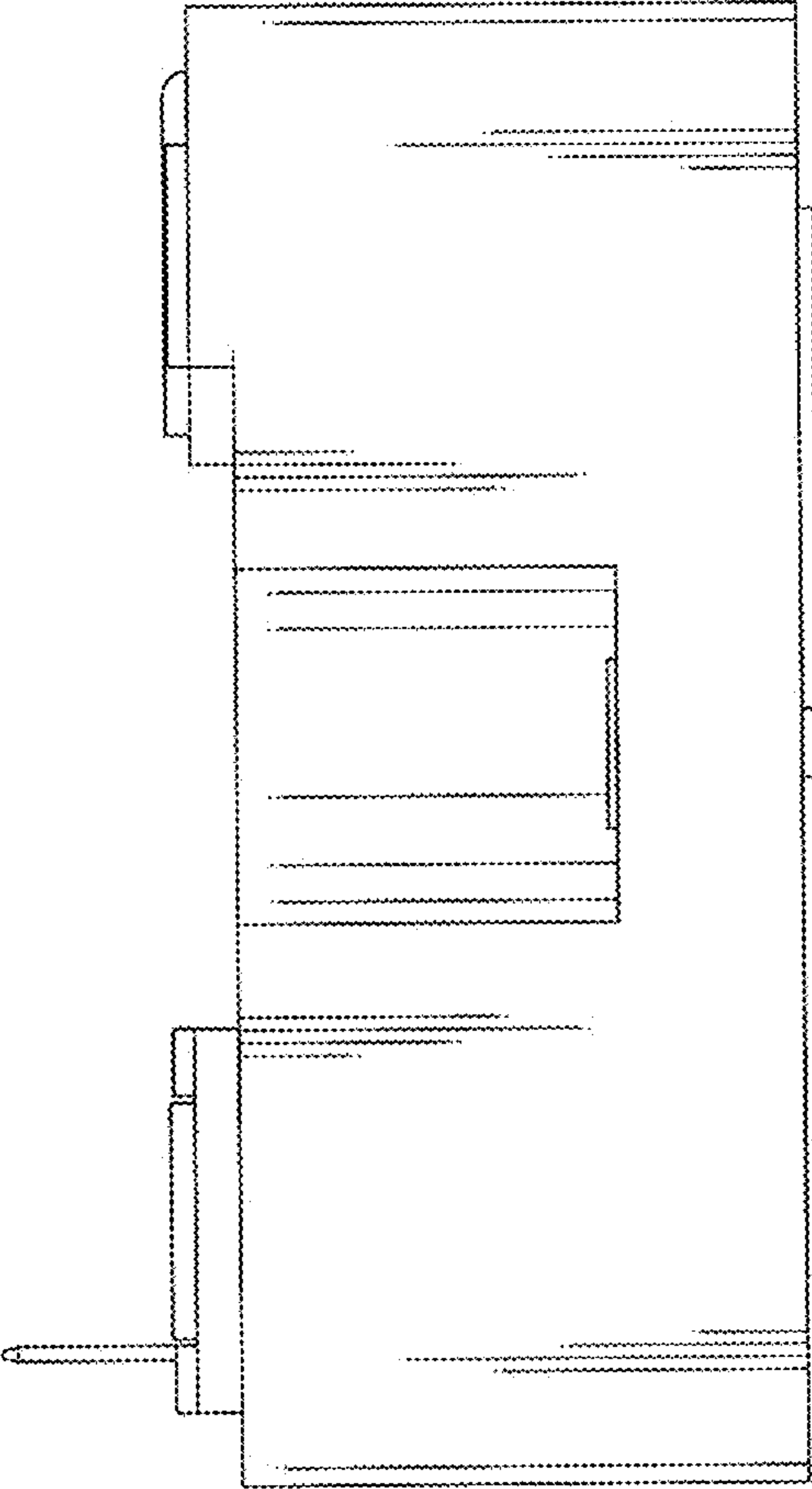


Fig. 5

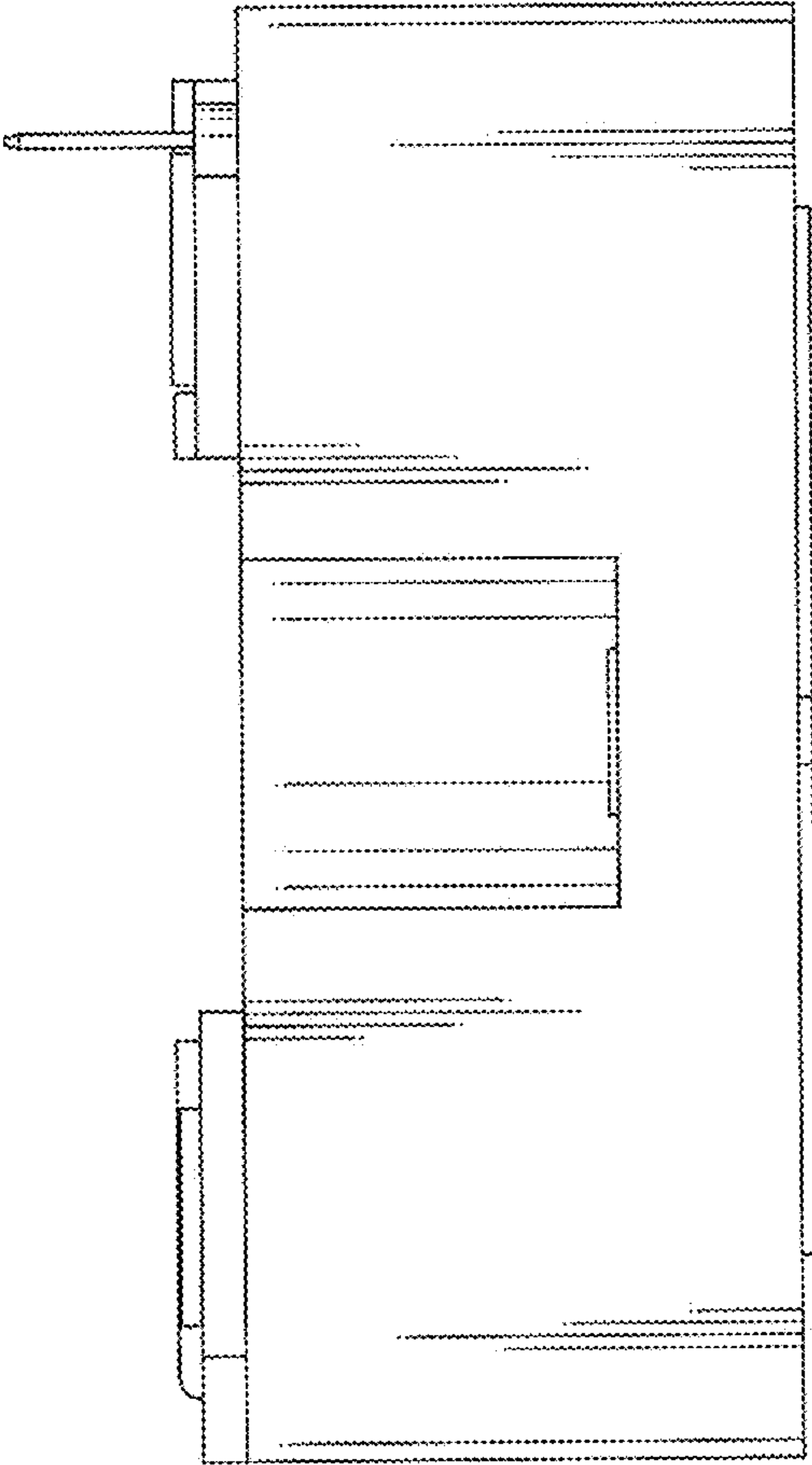


Fig. 6

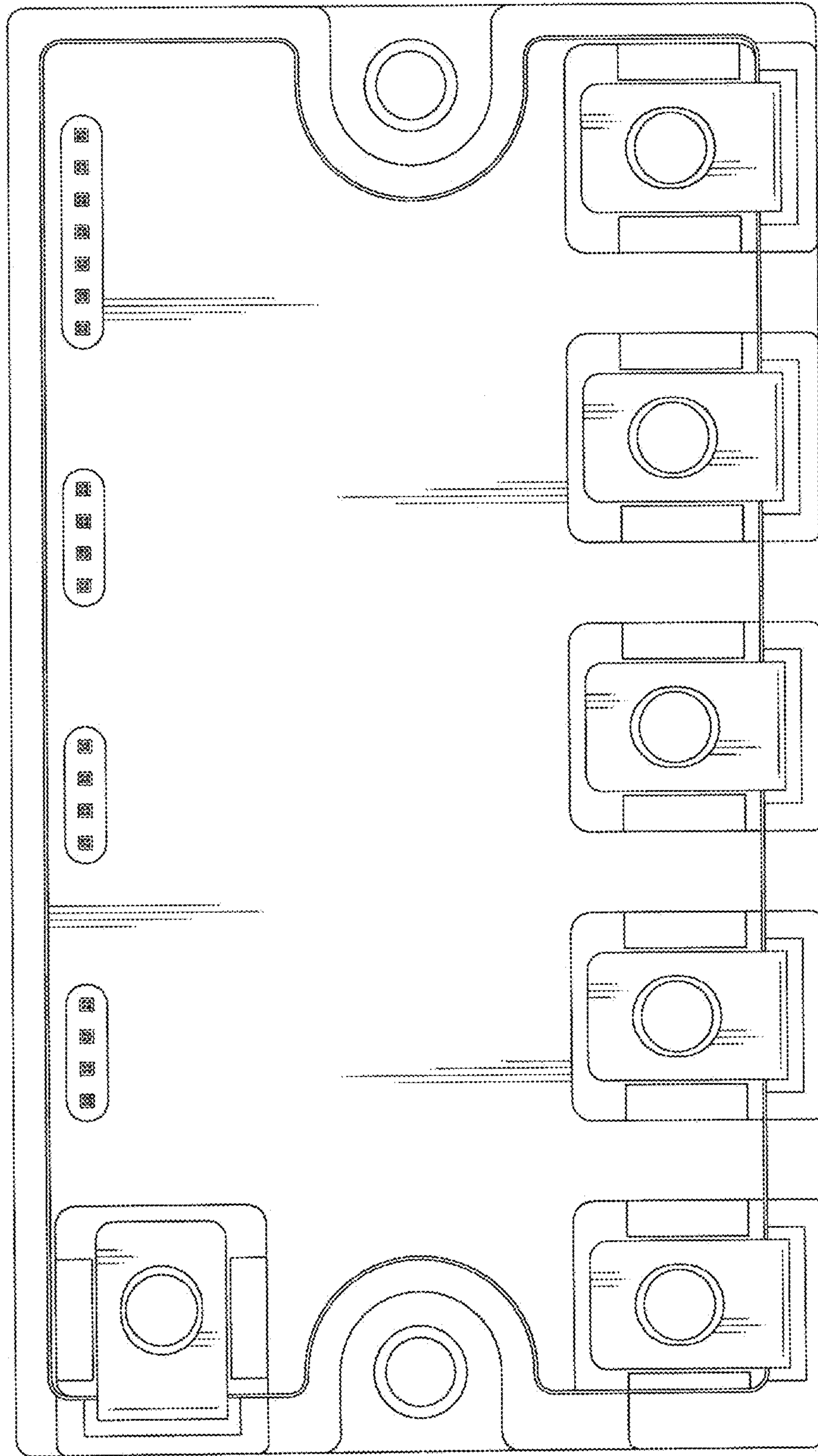


Fig. 7

